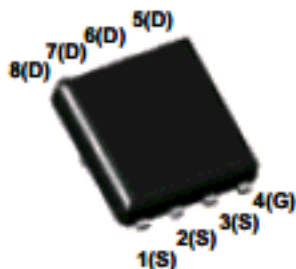


General Description

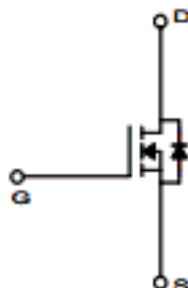
The MDU2657 uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDU2657 is suitable device for DC/DC Converter and general purpose applications.

Features

- $V_{DS} = 30V$
- $I_D = 61.7A @ V_{GS} = 10V$
- $R_{DS(on)}$
 $< 7.5m\Omega @ V_{GS} = 10V$
 $< 11.3m\Omega @ V_{GS} = 4.5V$
- 100% UIL Tested
- 100% Rg Tested



PowerDFN56

Absolute Maximum Ratings ($T_a = 25^{\circ}C$)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ⁽¹⁾	$T_C = 25^{\circ}C$	I_D	61.7	A
	$T_C = 70^{\circ}C$		49.3	
	$T_A = 25^{\circ}C$		20.4 ⁽²⁾	
	$T_A = 70^{\circ}C$		16.3 ⁽²⁾	
Pulsed Drain Current		I_{DM}	100	A
Power Dissipation	$T_C = 25^{\circ}C$	P_D	50	W
	$T_C = 70^{\circ}C$		32	
	$T_A = 25^{\circ}C$		5.5 ⁽²⁾	
	$T_A = 70^{\circ}C$		3.5 ⁽²⁾	
Single Pulse Avalanche Energy ⁽¹⁾		E_{AS}	81	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	$^{\circ}C$

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	22.7	$^{\circ}C/W$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	